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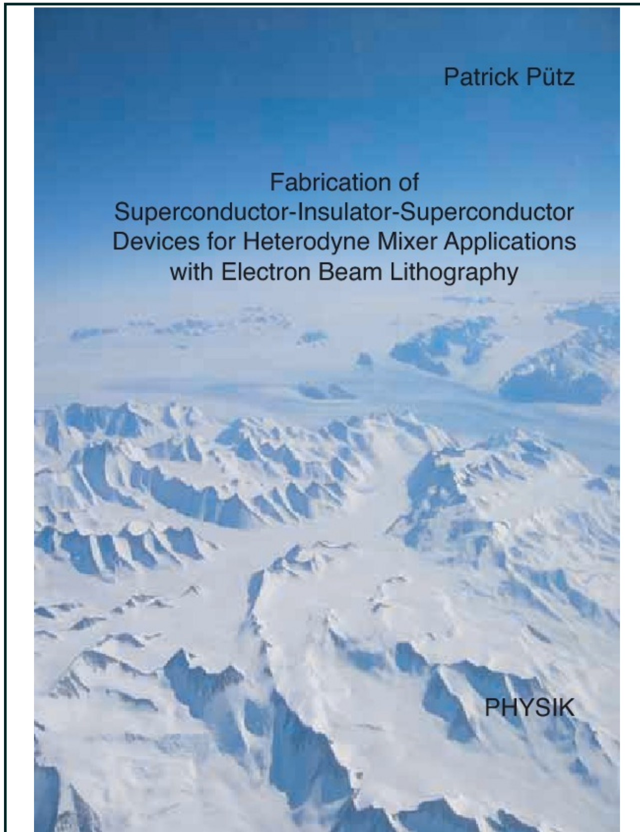
Fabrication of Superconductor-Insulator-Superconductor Devices for Heterodyne Mixer Applications with Electron Beam Lithography



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